

## ABSTRACT OF THE INVENTION

Nitride based semiconductor light-emitting devices with a sufficiently low contact resistance p-type electrode and a method of manufacturing the same are disclosed. One such method of manufacturing nitride based semiconductor light-emitting devices includes steps of growing island-like AlGaN films 17 on p-type nitride based semiconductor layer 16, etching a surface of p-type nitride based semiconductor layer 16 to make uneven portions 18 on its surface by using island-like AlGaN films 17 as a photomask, and forming of a p-type ohmic electrode on an electrode forming region of the uneven portion 18.

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